BU406, BU407

NPN Power Transistors

These devices are high voltage, high speed transistors for horizontal deflection output stages of TV's and CRT's.

Features

- High Voltage
- Fast Switching Speed
- Low Saturation Voltage
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	BU406 BU407	V _{CEO}	200 150	Vdc
Collector-Emitter Voltage	BU406 BU407	V _{CEV}	400 330	Vdc
Collector-Base Voltage	BU406 BU407	V _{CBO}	400 330	Vdc
Emitter-Base Voltage		V _{EBO}	6	Vdc
Collector Current – Continuous – Peak Repetitiv	е	I _C	7 10	Adc
Collector Current - Peak (10 ms)		I _{CM}	15	Adc
Base Current		I _B	4	Adc
Total Device Dissipation @ T _C = 25 Derate above 25°C	5°C	P _D	60 0.48	W W/°C
Operating and Storage Junction Temperature Storage		T _J , T _{stg}	-65 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.08	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	70	°C/W
Maximum Lead Temperature for Soldering Purposes1/8" from Case for 5 Seconds	TL	260	°C

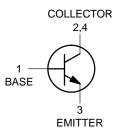


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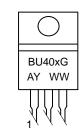
NPN SILICON POWER TRANSISTORS 7 AMPERES – 60 WATTS 150 AND 200 VOLTS

SCHEMATIC





MARKING DIAGRAM



BU40x = Specific Device Code

x = 6 or 7

A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BU406G	TO-220AB (Pb-Free)	50 Units / Rail
BU407G	TO-220AB (Pb-Free)	50 Units / Rail

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BU406, BU407

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector–Emitter Sustaining Voltage (Note 1) (I _C = 100 mAdc, I _B = 0)	BU406 BU407	V _{CEO(sus)}	200 150	_ _	_ _	Vdc	
Collector Cutoff Current		I _{CES}	- - -	- - -	5 0.1 1	mAdc	
Emitter Cutoff Current (V _{EB} = 6 Vdc, I _C = 0)	BU406, BU407	I _{EBO}	-	_	1	mAdc	
ON CHARACTERISTICS (Note 1)							
Collector–Emitter Saturation Voltage (I _C = 5 Adc, I _B = 0.5 Adc)		V _{CE(sat)}	_	_	1	Vdc	
Base–Emitter Saturation Voltage (I _C = 5 Adc, I _B = 0.5 Adc)		V _{BE(sat)}	-	_	1.2	Vdc	
Forward Diode Voltage (I _{EC} = 5 Adc) "D" only		V _{EC}	-	_	2	Volts	
DYNAMIC CHARACTERISTICS							
Current–Gain – Bandwidth Product (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f _{test} = 20 MHz)		f _T	10	-	_	MHz	
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1 MHz)		C _{ob}	_	80	_	pF	
SWITCHING CHARACTERISTICS	<u>.</u>		•		•	•	
Inductive Load Crossover Time $(V_{CC} = 40 \text{ Vdc}, I_C = 5 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ Adc}, L_{CC} = 0.5 \text{ Adc}$	_ = 150 μH)	t _c	_	_	0.75	μs	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

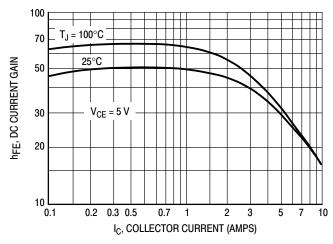


Figure 1. DC Current Gain

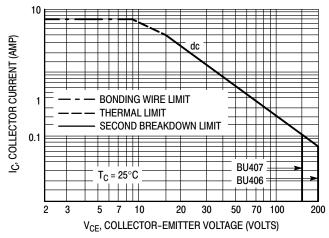
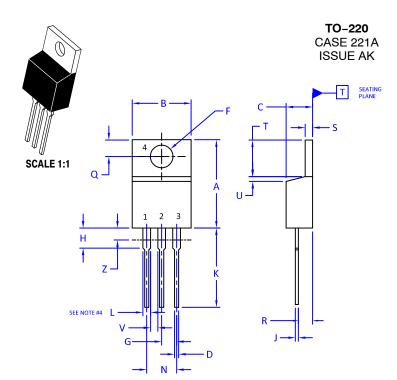


Figure 2. Maximum Rated Forward Bias Safe Operating Area

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1%.





DATE 13 JAN 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMI	ETERS
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	STYLE 6: PIN 1. 2. 3. 4.	CATHODE ANODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.			GATE SOURCE DRAIN SOURCE	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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